



16N68-ML

Preliminary

Power MOSFET

16A, 680V N-CHANNEL POWER MOSFET

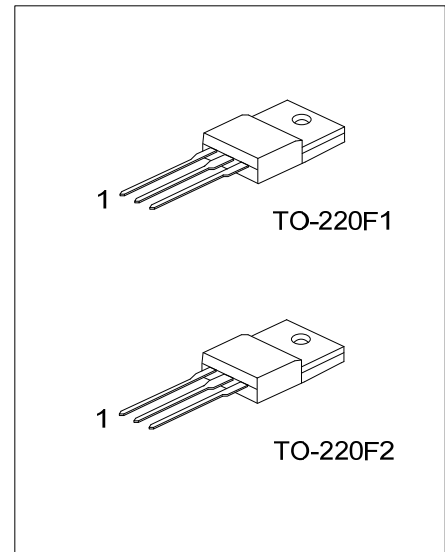
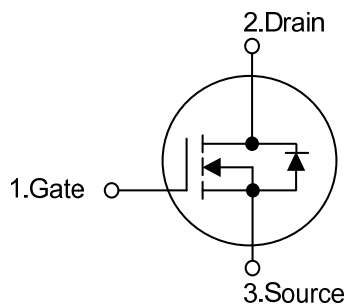
DESCRIPTION

The UTC **16N68-ML** is a high voltage power MOSFET combines advanced trench MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)} \leq 0.6 \Omega$ @ $V_{GS}=10V$, $I_D=8.0A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL



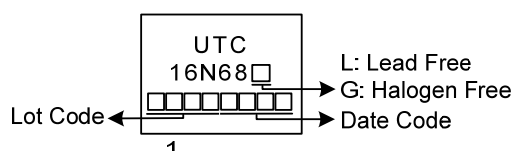
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
16N68L-TF1-T	16N68G-TF1-T	TO-220F1	G	D	S	Tube
16N68L-TF2-T	16N68G-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>16N68G-TF1-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube</p> <p>(2) TF1: TO-220F1, TF2: TO-220F2</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DS}	680	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	16	A
Pulsed Drain Current (Note 2)	I_{DM}	32	A
Avalanche Energy	E_{AS}	522	mJ
Single Pulsed (Note 3)			
Peak Diode Recovery dv/dt (Note 4)	dv/dt	1.1	V/ns
Power Dissipation	P_D	39	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 30\text{mH}$, $I_{AS} = 3.9\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD} \leq 16\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	3.2	$^{\circ}\text{C}/\text{W}$

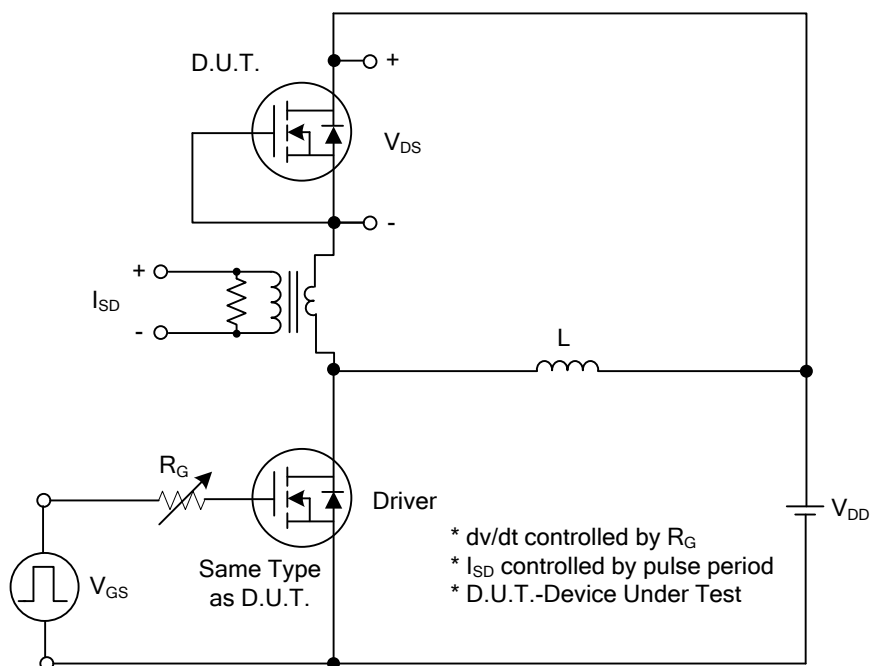
■ ELECTRICAL CHARACTERISTICS ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	680			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =680V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =8.0A			0.6	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		2450		pF
Output Capacitance		C _{OSS}			205		pF
Reverse Transfer Capacitance		C _{RSS}			9		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =400V, V _{GS} =10V, I _D =16A (Note 1, 2)		62		nC
Gate-Source Charge		Q _{GS}			16		nC
Gate-Drain Charge		Q _{GD}			18		nC
Turn-On Delay Time (Note 1)		t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =16A, R _G =25Ω (Note 1, 2)		32		ns
Turn-On Rise Time		t _R			21		ns
Turn-Off Delay Time		t _{D(OFF)}			166		ns
Turn-Off Fall Time		t _F			42		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Maximum Body-Diode Continuous Current		I _S				16	A
Maximum Body-Diode Pulsed Current		I _{SM}				32	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =16A , V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	I _S =16A , V _{GS} =0V		450		ns
Reverse Recovery Charge		Q _{rr}	di/dt=100A/μs		6.6		μC

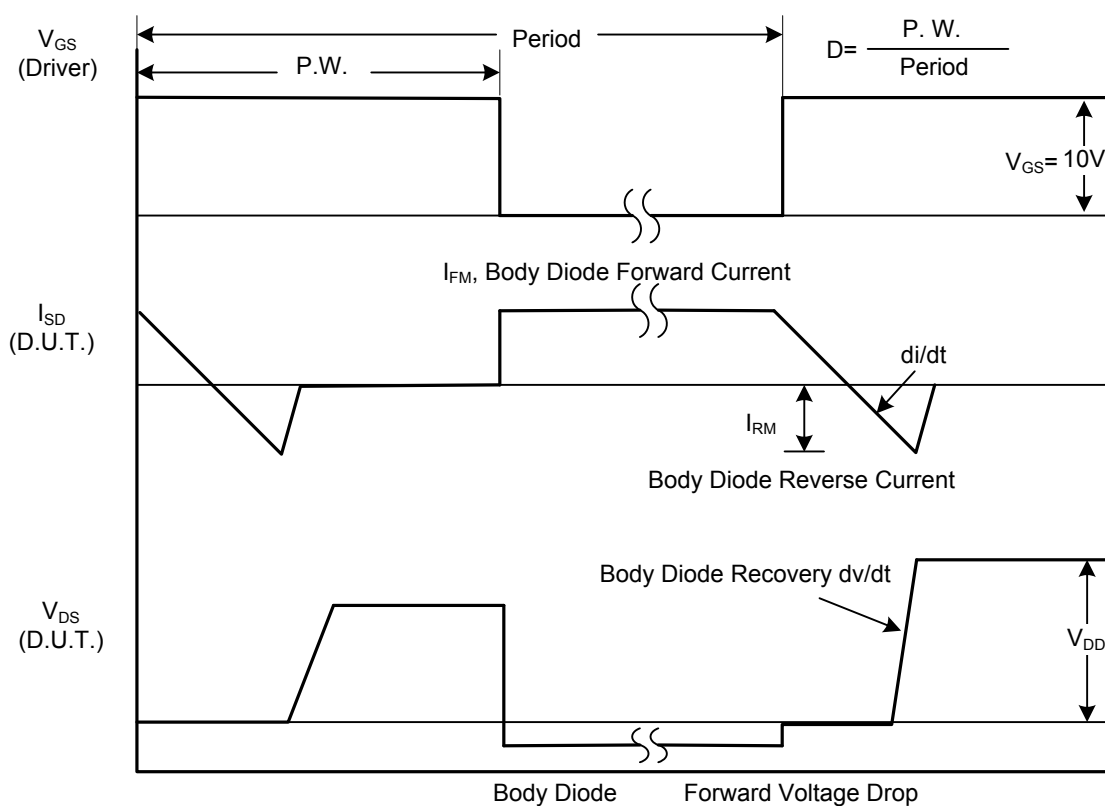
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

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